

# 128-Kbit (16K × 8) Serial (I<sup>2</sup>C) F-RAM

### **Features**

- 128-Kbit ferroelectric random access memory (F-RAM) logically organized as 16K × 8
  - ☐ High-endurance 100 trillion (10<sup>14</sup>) read/writes
  - □ 151-year data retention (See Data Retention and Endurance on page 13)
  - □ NoDelay™ writes
  - Advanced high-reliability ferroelectric process
- Fast two-wire serial interface (I<sup>2</sup>C)
  - □ Up to 3.4-MHz frequency<sup>[1]</sup>
  - □ Direct hardware replacement for serial EEPROM
  - □ Supports legacy timings for 100 kHz and 400 kHz
- Device ID
  - Manufacturer ID and Product ID
- Low power consumption
  - □ 175-µA active current at 100 kHz
  - □ 150-μA standby current
  - □ 8-µA sleep mode current
- Low-voltage operation: V<sub>DD</sub> = 2.0 V to 3.6 V
- Industrial temperature: -40 °C to +85 °C
- 8-pin small outline integrated circuit (SOIC) package
- Restriction of hazardous substances (RoHS) compliant

## **Functional Description**

The FM24V01A is a 128-Kbit nonvolatile memory employing an advanced ferroelectric process. An F-RAM is nonvolatile and performs reads and writes similar to a RAM. It provides reliable data retention for 151 years while eliminating the complexities, overhead, and system-level reliability problems caused by EEPROM and other nonvolatile memories.

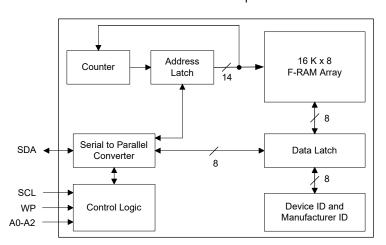
Unlike EEPROM, the FM24V01A performs write operations at bus speed. No write delays are incurred. Data is written to the memory array immediately after each byte is successfully transferred to the device. The next bus cycle can commence without the need for data polling. In addition, the product offers substantial write endurance compared with other nonvolatile memories. F-RAM also exhibits much lower power during writes than EEPROM because write operations do not require an internally elevated power supply voltage for write circuits. The FM24V01A is capable of supporting 10<sup>14</sup> read/write cycles, or 100 million times more write cycles than EEPROM.

These capabilities make the FM24V01A ideal for nonvolatile memory applications, requiring frequent or rapid writes. Examples range from data logging, where the number of write cycles may be critical, to demanding industrial controls where the long write time of EEPROM can cause data loss. The combination of features allows more frequent data writing with less overhead for the system.

The FM24V01A provides substantial benefits to users of serial EEPROM as a hardware drop-in replacement. The device incorporates a read-only Device ID that allows the host to determine the manufacturer, product density, and product revision. The device specifications are guaranteed over an industrial temperature range of -40~°C to +85~°C.

For a complete list of related resources, click here.

## Logic Block Diagram



### Note

The FM24V01A does not meet the NXP I<sup>2</sup>C specification in the Fast-mode Plus (Fm+, 1 MHz) for I<sub>OL</sub> and in the High Speed Mode (Hs-mode, 3.4 MHz) for V<sub>hys</sub>. Refer to DC Electrical Characteristics on page 12 for more details.



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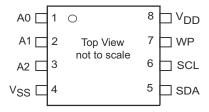
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## **Pinout**

Figure 1. 8-pin SOIC Pinout



## **Pin Definitions**

Pin Name	I/O Type	Description
A0-A2	Input	<b>Device Select Address 0–2</b> . These pins are used to select one of up to eight devices of the same type on the same two-wire bus. To select the device, the address value on the three pins must match the corresponding bits contained in the slave address. The address pins are pulled down internally.
SDA	Input/Output	<b>Serial Data Address</b> . This is a bidirectional pin for the two-wire interface. It is open-drain and is intended to be wire-AND'd with other devices on the two-wire bus. The input buffer incorporates a Schmitt trigger for noise immunity and the output driver includes slope control for falling edges. An external pull-up resistor is required.
SCL	Input	<b>Serial Clock</b> . The serial clock pin for the two-wire interface. Data is clocked out of the part on the falling edge, and into the device on the rising edge. The SCL input also incorporates a Schmitt trigger input for noise immunity.
WP	Input	<b>Write Protect</b> . When tied to $V_{DD}$ , addresses in the entire memory map will be write-protected. When WP is connected to ground, all addresses are write enabled. This pin is pulled down internally.
V <sub>SS</sub>	Power supply	Ground for the device. Must be connected to the ground of the system.
$V_{DD}$	Power supply	Power supply input to the device.

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### **Functional Overview**

The FM24V01A is a serial F-RAM memory. The memory array is logically organized as 16,384  $\times$  8 bits and is accessed using a two-wire ( $^{12}$ C) interface. The functional operation of the F-RAM is similar to serial EEPROM. The major difference between the FM24V01A and a serial EEPROM with the same pinout is the F-RAM's superior write performance, high endurance, and low power consumption.

## **Memory Architecture**

When accessing the FM24V01A, the user addresses 16K locations of eight data bits each. These eight data bits are shifted in or out serially. The addresses are accessed using the two-wire protocol, which includes a slave address (to distinguish other non-memory devices) and a two-byte address. The upper 2 bits of the address range are 'don't care' values. The complete address of 14 bits specifies each byte address uniquely.

The access time for the memory operation is essentially zero, beyond the time needed for the serial protocol. That is, the memory is read or written at the speed of the two-wire bus. Unlike a serial EEPROM, it is not necessary to poll the device for a ready condition because writes occur at bus speed. By the time a new bus transaction can be shifted into the device, a write

operation is complete. This is explained in more detail in the Memory Operation on page 8.

### **Two-wire Interface**

The FM24V01A employs a bidirectional two-wire bus protocol using few pins or board space. Figure 2 illustrates a typical system configuration using the FM24V01A in a microcontroller-based system. The two-wire bus is familiar to many users but is described in this section.

By convention, any device that is sending data to the bus is the transmitter while the target device for this data is the receiver. The device that is controlling the bus is the master. The master is responsible for generating the clock signal for all operations. Any device on the bus that is being controlled is a slave. The FM24V01A is always a slave device.

The bus protocol is controlled by transition states in the SDA and SCL signals. There are four conditions including START, STOP, data bit, or acknowledge. Figure 3 on page 5 and Figure 4 on page 5 illustrate the signal conditions that specify the four states. Detailed timing diagrams are shown in the electrical specifications section.

The FM24V01A does not meet the NXP  $I^2$ C specification in the Fast-mode Plus (Fm+, 1 MHz) for  $I_{OL}$  and in the High Speed Mode (Hs-mode, 3.4 MHz) for  $V_{hys}$ . Refer to DC Electrical Characteristics on page 12 for more details.

 $R_{Pmin} = (V_{DD} - V_{OI} max) / I_{OI}$  $R_{Pmax} = t_r / (0.8473 * C_b)$ SDA Microcontroller SCI  $V_{DD}$  $V_{DD}$ ΑO SCI ΑO SCI AΩ SCI Α1 A1 SDA SDA A1 SDA A2 A2 A2 WF WP WF FM24V01A FM24V01A FM24V01A #1 #0 #7

Figure 2. System Configuration Using Serial (I<sup>2</sup>C) F-RAM



## STOP Condition (P)

A STOP condition is indicated when the bus master drives SDA from LOW to HIGH while the SCL signal is HIGH. All operations using the FM24V01A should end with a STOP condition. If an operation is in progress when a STOP is asserted, the operation will be aborted. The master must have control of the SDA (not a memory read) to assert a STOP condition.

## **START Condition (S)**

A START condition is indicated when the bus master drives SDA from HIGH to LOW while the SCL signal is HIGH. All commands should be preceded by a START condition. An operation in progress can be aborted by asserting a START condition at any time. Aborting an operation using the START condition will ready the FM24V01A for a new operation.

If during operation the power supply drops below the specified  $V_{DD}$  minimum, the system should issue a START condition prior to performing another operation.

SDA

START Condition

Figure 3. START and STOP Conditions

SDA

SCL

START Condition

STOP Condition

### **Data/Address Transfer**

All data transfers (including addresses) take place while the SCL signal is HIGH. Except under the three conditions described above, the SDA signal should not change while SCL is HIGH.

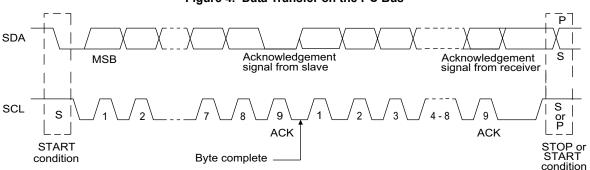


Figure 4. Data Transfer on the I<sup>2</sup>C Bus



### Acknowledge/No-acknowledge

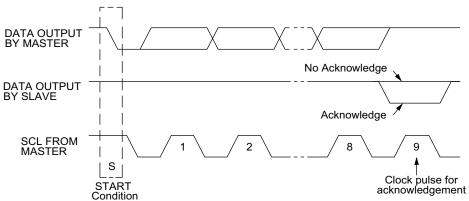
The acknowledge takes place after the 8th data bit has been transferred in any transaction. During this state, the transmitter should release the SDA bus to allow the receiver to drive it. The receiver drives the SDA signal LOW to acknowledge receipt of the byte. If the receiver does not drive SDA LOW, the condition is a no-acknowledge and the operation is aborted.

The receiver will fail to acknowledge for two distinct reasons, the first being that a byte transfer fails. In this case, the no-acknowledge ceases the current operation so that the part

can be addressed again. This allows the last byte to be recovered in the event of a communication error.

The second and most common reason is that, the receiver does not acknowledge to deliberately end an operation. For example, during a read operation, the FM24V01A will continue to place data on the bus as long as the receiver sends acknowledges (and clocks). When a read operation is complete and no more data is needed, the receiver must not acknowledge the last byte. If the receiver acknowledges the last byte, this causes the FM24V01A to attempt to drive the bus on the next clock while the master is sending a new command such as STOP.



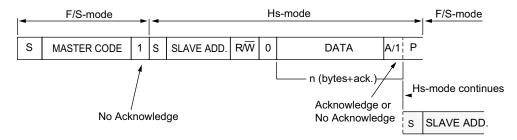


### **High Speed Mode (Hs-mode)**

The FM24V01A supports a 3.4-MHz high-speed mode. A master code (00001XXXb) must be issued to place the device into the

high-speed mode. Communication between master and slave will then be enabled for speeds up to 3.4 MHz. A STOP condition will exit Hs-mode. Single- and multiple-byte reads and writes are supported.

Figure 6. Data Transfer Format in Hs-Mode





### Slave Device Address

The first byte that the FM24V01A expects after a START condition is the slave address. As shown in Figure 7, the slave address contains the device type or slave ID, the device select address bits, and a bit that specifies if the transaction is a read or a write.

Bits 7–4 are the device type (slave ID) and should be set to 1010b for the FM24V01A. These bits allow other function types to reside on the two-wire bus within an identical address range. Bits 3–1 are the device select address bits. They must match the corresponding value on the external address pins to select the device. Up to eight FM24V01A devices can reside on the same two-wire bus by assigning a different address to each. Bit 0 is the read/write bit (R/W). R/W = '1' indicates a read operation and R/W = '0' indicates a write operation.

Figure 7. Memory Slave Device Address



### **Addressing Overview**

After the FM24V01A (as receiver) acknowledges the slave address, the master can place the memory address on the bus for a write operation. The address requires two bytes. The

complete 14-bit address is latched internally. Each access causes the latched address value to be incremented automatically. The current address is the value that is held in the latch; either a newly written value or the address following the last access. The current address will be held for as long as power remains or until a new value is written. Reads always use the current address. A random read address can be loaded by beginning a write operation as explained below.

After transmission of each data byte, just prior to the acknowledge, the FM24V01A increments the internal address latch. This allows the next sequential byte to be accessed with no additional addressing. After the last address (3FFFh) is reached, the address latch will roll over to 0000h. There is no limit to the number of bytes that can be accessed with a single read or write operation.

### **Data Transfer**

After the address bytes have been transmitted, data transfer between the bus master and the FM24V01A can begin. For a read operation the FM24V01A will place 8 data bits on the bus then wait for an acknowledge from the master. If the acknowledge occurs, the FM24V01A will transfer the next sequential byte. If the acknowledge is not sent, the FM24V01A will end the read operation. For a write operation, the FM24V01A will accept 8 data bits from the master then sends an acknowledge. All data transfer occurs MSB (most significant bit) first

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## **Memory Operation**

The FM24V01A is designed to operate in a manner very similar to other two-wire interface memory products. The major differences result from the higher performance write capability of F-RAM technology. These improvements result in some differences between the FM24V01A and a similar configuration EEPROM during writes. The complete operation for both writes and reads is explained in the following sections.

## **Write Operation**

All writes begin with a slave address, then a memory address. The bus master indicates a write operation by setting the LSB of the slave address (R/W bit) to a '0'. After addressing, the bus master sends each byte of data to the memory and the memory generates an acknowledge condition. Any number of sequential bytes may be written. If the end of the address range is reached internally, the address counter will wrap from 3FFFh to 0000h.

Unlike other nonvolatile memory technologies, there is no effective write delay with F-RAM. Since the read and write access times of the underlying memory are the same, the user experiences no delay through the bus. The entire memory cycle

occurs in less time than a single bus clock. Therefore, any operation including read or write can occur immediately following a write. Acknowledge polling, a technique used with EEPROMs to determine if a write is complete is unnecessary and will always return a ready condition.

Internally, an actual memory write occurs after the 8th data bit is transferred. It will be complete before the acknowledge is sent. Therefore, if the user desires to abort a write without altering the memory contents, this should be done using START or STOP condition prior to the 8th data bit. The FM24V01A uses no page buffering.

The memory array can be write-protected using the WP pin. Setting the WP pin to a HIGH condition ( $V_{DD}$ ) will write-protect all addresses. The FM24V01A will not acknowledge data bytes that are written to protected addresses. In addition, the address counter will not increment if writes are attempted to these addresses. Setting WP to a LOW state ( $V_{SS}$ ) will disable the write protect. WP is pulled down internally.

Figure 8 and Figure 9 illustrate a single-byte and multiple-byte write cycles in Fast-mode Plus (Fm+). Figure 10 illustrates a single-byte write cycles in Hs mode.

Figure 8. Single-Byte Write

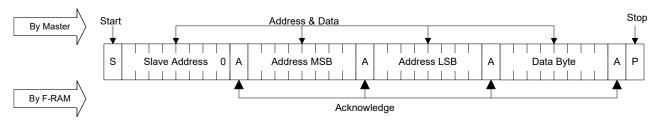


Figure 9. Multi-Byte Write

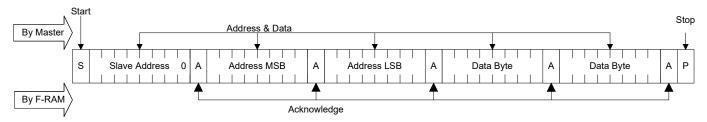
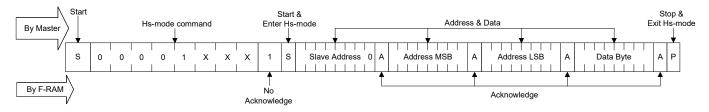


Figure 10. Hs-Mode Byte Write





### **Read Operation**

There are two basic types of read operations. They are current address read and selective address read. In a current address read, the FM24V01A uses the internal address latch to supply the address. In a selective read, the user performs a procedure to set the address to a specific value.

### Current Address & Sequential Read

As mentioned in the previous paragraph, the FM24V01A uses an internal latch to supply the address for a read operation. A current address read uses the existing value in the address latch as a starting place for the read operation. The system reads from the address immediately following that of the last operation.

To perform a current address read, the bus master supplies a slave address with the LSB set to a '1'. This indicates that a read operation is requested. After receiving the complete slave address, the FM24V01A will begin shifting out data from the current address on the next clock. The current address is the value held in the internal address latch.

Beginning with the current address, the bus master can read any number of bytes. Thus, a sequential read is simply a current address read with multiple byte transfers. After each byte the internal address counter will be incremented.

**Note** Each time the bus master acknowledges a byte, this indicates that the FM24V01A should read out the next sequential byte.

There are four ways to properly terminate a read operation. Failing to properly terminate the read will most likely create a bus contention as the FM24V01A attempts to read out additional data onto the bus. The four valid methods are:

- The bus master issues a no-acknowledge in the 9th clock cycle and a STOP in the 10th clock cycle. This is illustrated in the following diagrams. This method is preferred.
- 2. The bus master issues a no-acknowledge in the 9th clock cycle and a START in the 10th.
- 3. The bus master issues a STOP in the 9th clock cycle.
- 4. The bus master issues a START in the 9th clock cycle.

Figure 11. Current Address Read

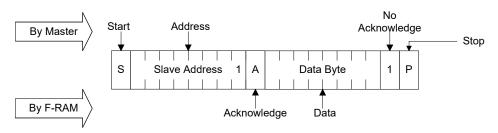


Figure 12. Sequential Read

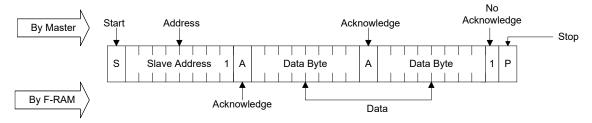
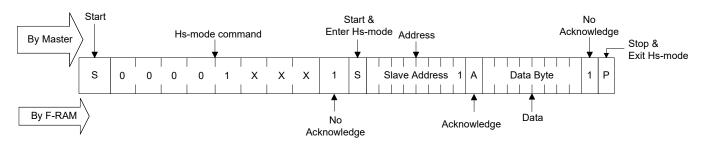


Figure 13. Hs-Mode Current Address Read



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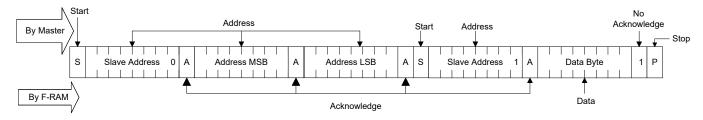


### Selective (Random) Read

There is a simple technique that allows a user to select a random address location as the starting point for a read operation. This involves using the first three bytes of a write operation to set the internal address followed by subsequent read operations.

To perform a selective read, the bus master sends out the slave address with the LSB (R/W) set to 0. This specifies a write operation. According to the write protocol, the bus master then sends the address bytes that are loaded into the internal address latch. After the FM24V01A acknowledges the address, the bus master issues a START condition. This simultaneously aborts the write operation and allows the read command to be issued with the slave address LSB set to a '1'. The operation is now a current address read.

Figure 14. Selective (Random) Read



### Sleep Mode

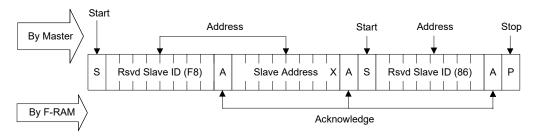
A low-power mode called Sleep Mode is implemented on the FM24V01A device. The device will enter this low power state when the Sleep command 86h is clocked-in. Sleep Mode entry can be entered as follows:

- 1. The master sends a START command.
- 2. The master sends Reserved Slave ID 0xF8.
- 3. The FM24V01A sends an ACK.
- 4. The master sends the I<sup>2</sup>C-bus slave address of the slave device it needs to identify. The last bit is a 'Don't care' value (R/W bit). Only one device must acknowledge this byte (the one that has the I<sup>2</sup>C-bus slave address).
- 5. The FM24V01A sends an ACK.

- 6. The master sends a Re-START command.
- 7. The master sends Reserved Slave ID 0x86.
- 8. The FM24V01A sends an ACK.
- The master sends STOP to ensure the device enters sleep mode.

Once in sleep mode, the device draws  $I_{ZZ}$  current, but the device continues to monitor the  $I^2C$  pins. Once the master sends a Slave Address that the FM24V01A identifies, it will "wake-up" and be ready for normal operation within  $t_{REC}$  (400  $\mu$ s max.). As an alternative method of determining when the device is ready, the master can send read or write commands and look for an ACK. While the device is waking up, it will NACK the master until it is ready.

Figure 15. Sleep Mode Entry





### **Device ID**

The FM24V01A device incorporates a means of identifying the device by providing three bytes of data, which are manufacturer, product ID, and die revision. The Device ID is read-only. It can be accessed as follows:

- 1. The master sends a START command.
- 2. The master sends Reserved Slave ID 0xF8.
- 3. The FM24V01A sends an ACK.
- 4. The master sends the I<sup>2</sup>C-bus slave address of the slave device it needs to identify. The last bit is a 'Don't care' value (R/W bit). Only one device must acknowledge this byte (the one that has the I<sup>2</sup>C-bus slave address).
- 5. The FM24V01A sends an ACK.

- 6. The master sends a Re-START command.
- 7. The master sends Reserved Slave ID 0xF9.
- 8. The FM24V01A sends an ACK.
- 9. The Device ID Read can be done, starting with the 12 manufacturer bits, followed by the 9 part identification bits, and then the 3 die revision bits.
- 10. The master ends the Device ID read sequence by NACKing the last byte, thus resetting the slave device state machine and allowing the master to send the STOP command.

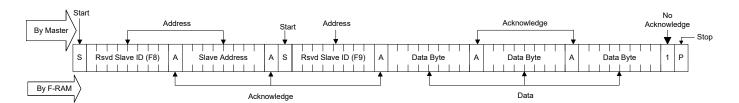
Note The reading of the Device ID can be stopped anytime by sending a NACK command.

Table 1. Device ID

	Device	ID Description				
Device ID (3 bytes)	23–12 (12 bits)	11–8 (4 bits)	7–3 (5 bits)	2–0 (3 bits)		
(3 bytes)	Manufacturer ID	Product ID				
	Manufacturer 15	Density	Variation	Die Rev		
004101h	00000000100	0001	00000	001		

Note Product ID bits 0 and 4 are reserved.

Figure 16. Read Device ID



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## **Maximum Ratings**

Exceeding maximum ratings may shorten the useful life of the device. These user quidelines are not tested

device. These user guidelines are not tested.
Storage temperature65 °C to +125 °C
Maximum accumulated storage time At 125 °C ambient temperature
Ambient temperature with power applied–55 °C to +125 °C
Supply voltage on $V_{DD}$ relative to $V_{SS}$ –1.0 V to +4.5 V
Input voltage* –1.0 V to + 4.5 V and $V_{\text{IN}}$ < $V_{\text{DD}}$ + 1.0 V
DC voltage applied to outputs in HI-Z state0.5 V to $\rm V_{DD}$ + 0.5 V
Transient voltage (< 20 ns)

on any pin to ground potential ......-2.0 V to  $V_{DD}$  + 2.0 V

Package power dissipation capability (T <sub>A</sub> = 25 °C)
Surface mount lead soldering temperature (3 seconds)+260°C
Electrostatic discharge voltage  Human Body Model (JEDEC Std JESD22-A114-B)
Latch-up current> 140 mA
$^{\star}$ Exception: The "V $_{\rm IN}$ < V $_{\rm DD}$ + 1.0 V" restriction does not apply to the SCL and SDA inputs.

## **Operating Range**

Range	Ambient Temperature (T <sub>A</sub> )	V <sub>DD</sub>
Industrial	–40 °C to +85 °C	2.0 V to 3.6 V

## **DC Electrical Characteristics**

Over the Operating Range

Parameter	Description	Test Cond	ditions	Min	<b>Typ</b> [2]	Max	Unit
$V_{DD}$	Power supply			2.0	3.3	3.6	V
I <sub>DD</sub>	Average V <sub>DD</sub> current	SCL toggling between	f <sub>SCL</sub> = 100 kHz	_	_	175	μΑ
		V <sub>DD</sub> – 0.2 V and V <sub>SS</sub> , other inputs V <sub>SS</sub> or	f <sub>SCL</sub> = 1 MHz	_	_	400	μΑ
			f <sub>SCL</sub> = 3.4 MHz	_	-	1000	μΑ
I <sub>SB</sub>	V <sub>DD</sub> standby current	SCL = SDA = $V_{DD}$ . All $V_{DD}$ . Stop command is		_	90	150	μА
I <sub>ZZ</sub>	Sleep mode current	SCL = SDA = $V_{DD}$ . All $V_{DD}$ . Stop command is		_	5	8	μА
ILI	Input leakage current (Except WP and A2–A0)	$V_{SS} \le V_{IN} \le V_{DD}$		-1	ı	+1	μА
	Input leakage current (for WP and A2–A0)	$V_{SS} \le V_{IN} \le V_{DD}$		-1	-	+100	μА
I <sub>LO</sub>	Output leakage current	$V_{SS} \leq V_{OUT} \leq V_{DD}$		-1	-	+1	μΑ
V <sub>IH</sub>	Input HIGH voltage (SDL, SDA)			$0.7 \times V_{DD}$	_	$V_{DD(max)} + 0.3$	V
	Input HIGH voltage (WP, A2-A0)			0.7 × V <sub>DD</sub>	_	V <sub>DD</sub> + 0.3	V
$V_{IL}$	Input LOW voltage			-0.3	_	0.3 × V <sub>DD</sub>	V
V <sub>OL</sub> [3]	Output LOW voltage	I <sub>OL</sub> = 3 mA		_	1	0.4	V
		I <sub>OL</sub> = 6 mA		-	1	0.6	V
R <sub>in</sub> <sup>[4]</sup>	Input resistance (WP, A2–A0)	For V <sub>IN</sub> = V <sub>IL(Max)</sub>		50	_	_	kΩ
		For V <sub>IN</sub> = V <sub>IH(Min)</sub>		1	_	_	ΜΩ
V <sub>hys</sub> <sup>[5]</sup>	Hysteresis of Schmitt Trigger inputs		f <sub>SCL</sub> = 100 kHz, 400 kHz, 1 MHz	0.05 × V <sub>DD</sub>	-	_	V
			f <sub>SCL</sub> = 3.4 MHz	0.06 × V <sub>DD</sub>	_	_	V

- Typical values are at 25 °C, V<sub>DD</sub> = V<sub>DD</sub>(typ). Not 100% tested.
   Typical values are at 25 °C, V<sub>DD</sub> = V<sub>DD</sub>(typ). Not 100% tested.
   The FM24V01A does not meet the NXP I<sup>2</sup>C specification in the Fast-mode Plus (Fm+, 1 MHz) for I<sub>OL</sub> of 20 mA at a V<sub>OL</sub> of 0.4 V.
   The input pull-down circuit is strong (50 kΩ) when the input voltage is below V<sub>IL</sub> and weak (1 MΩ) when the input voltage is above V<sub>IH</sub>.
   The FM24V01A does not meet the NXP I<sup>2</sup>C specification in the High Speed Mode (Hs-mode, 3.4 MHz) for V<sub>hys</sub> of 0.1 × V<sub>DD</sub>.



## **Data Retention and Endurance**

Parameter	Description	Test condition	Min	Max	Unit
T <sub>DR</sub>	Data retention	T <sub>A</sub> = 85 °C	10	-	Years
		T <sub>A</sub> = 75 °C	38	-	
		T <sub>A</sub> = 65 °C	151	-	
NV <sub>C</sub>	Endurance	Over operating temperature	10 <sup>14</sup>	-	Cycles

## Capacitance

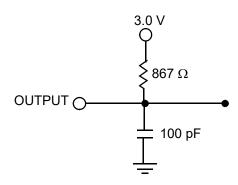
Parameter [6]	Description	Test Conditions	Max	Unit
C <sub>IO</sub>	Input/Output pin capacitance (SDA)	$T_A = 25 ^{\circ}\text{C}, f = 1 \text{MHz}, V_{DD} = V_{DD}(\text{typ})$	8	pF
C <sub>I</sub>	Input pin capacitance		6	pF

## **Thermal Resistance**

Parameter [6]	Description	Test Conditions	8-pin SOIC	Unit
$\Theta_{JA}$	Thermal resistance (junction to ambient)	Test conditions follow standard test methods and procedures for measuring thermal impedance, per	146	°C/W
$\Theta_{\sf JC}$	Thermal resistance (junction to case)	EIA/JESD51.	48	°C/W

## **AC Test Loads and Waveforms**

Figure 17. AC Test Loads and Waveforms



## **AC Test Conditions**

Input pulse levels	10% and 90% of V <sub>DD</sub>
Input rise and fall times	10 ns
Input and output timing reference lev	els0.5 × V <sub>DD</sub>
Output load capacitance	100 pF

### Note

6. These parameters are guaranteed by design and are not tested.

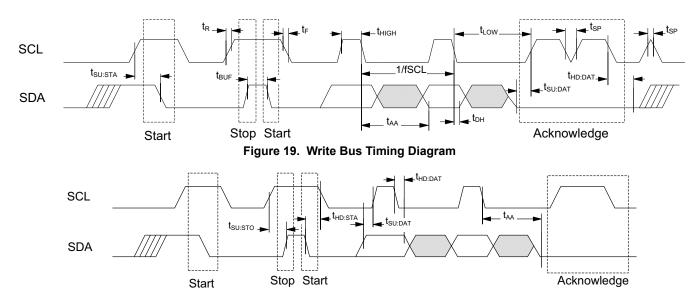


## **AC Switching Characteristics**

Over the Operating Range

Parameters <sup>[7]</sup>			Fast-mode Plus (Fm+) <sup>[9]</sup> Hs-mod			ode <sup>[9]</sup>		
Cypress Parameter	Alt. Parameter	Description	Min	Max	Min	Max	Unit	
f <sub>SCL</sub> <sup>[8]</sup>		SCL clock frequency	_	1.0	_	3.4	MHz	
t <sub>SU; STA</sub>		Start condition setup for repeated Start	260	-	160	_	ns	
t <sub>HD;STA</sub>		Start condition hold time	260	-	160	_	ns	
$t_{LOW}$		Clock LOW period	500	-	160	_	ns	
t <sub>HIGH</sub>		Clock HIGH period	260	-	60	_	ns	
t <sub>SU;DAT</sub>	t <sub>SU;DATA</sub>	Data in setup	up 50 –		10	_	ns	
t <sub>HD;DAT</sub>	t <sub>HD;DATA</sub>	Data in hold	0	-	0	70	ns	
t <sub>DH</sub>		Data output hold (from SCL at V <sub>IL</sub> )	0	-	0	_	ns	
t <sub>R</sub> <sup>[10]</sup>	t <sub>r</sub>	Input rise time	_	120	10	80	ns	
t <sub>F</sub> <sup>[10]</sup>	t <sub>f</sub>	Input fall time	20 × (V <sub>DD</sub> / 5.5 V)	120	10	80	ns	
t <sub>SU;STO</sub>		STOP condition setup	260		160	_	ns	
t <sub>AA</sub>	t <sub>VD;DATA</sub>	SCL LOW to SDA Data Out Valid	_	450	_	130	ns	
t <sub>VD;ACK</sub>		ACK output valid time	_	450	_	130	ns	
t <sub>OF</sub> <sup>[10]</sup>		Output fall time from V <sub>IH</sub> min to V <sub>IL</sub> max	20 × (V <sub>DD</sub> / 5.5 V)	120	_	80	ns	
t <sub>BUF</sub>		Bus free before new transmission	500 – 300 –		_	ns		
t <sub>SP</sub>		Noise suppression time constant on SCL, SDA	DA 0 50 – 5		5	ns		

Figure 18. Read Bus Timing Diagram



### Notes

- Test conditions assume signal transition time of 10 ns or less, timing reference levels of V<sub>DD</sub>/2, input pulse levels of 0 to V<sub>DD</sub>(typ), and output loading of the specified I<sub>OL</sub> and 100 pF load capacitance shown in Figure 17 on page 13.
   The speed-related specifications are guaranteed characteristic points along a continuous curve of operation from DC to f<sub>SCL</sub>(max).
   Bus Load (Cb) considerations; Cb < 550 pF for I<sup>2</sup>C clock frequency (SCL) 1 MHz; Cb < 100 pF for SCL at 3.4 MHz.</li>
   These parameters are guaranteed by design and are not tested.

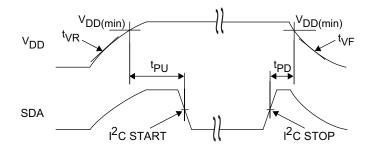


## **Power Cycle Timing**

Over the Operating Range

Parameter	Description	Min	Max	Unit
t <sub>PU</sub>	Power-up V <sub>DD</sub> (min) to first access (START condition)	250	_	μs
t <sub>PD</sub>	Last access (STOP condition) to power-down (V <sub>DD</sub> (min))	0	_	μs
t <sub>VR</sub> <sup>[11, 12]</sup>	V <sub>DD</sub> power-up ramp rate	50	_	μs/V
t <sub>VF</sub> [11, 12]	V <sub>DD</sub> power-down ramp rate	100	_	μs/V
t <sub>REC</sub>	Recovery time from sleep mode	_	400	μs

Figure 20. Power Cycle Timing



**Notes**11. Slope measured at any point on the V<sub>DD</sub> waveform.

<sup>12.</sup> These parameters are guaranteed by design and are not tested.

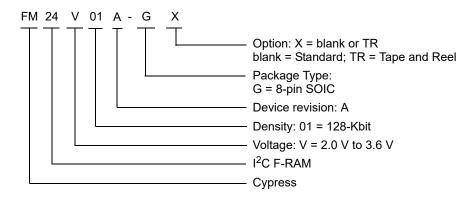


## **Ordering Information**

Ordering Code	Package Diagram	Package Type	Operating Range
FM24V01A-G	51-85066	8-pin SOIC	Industrial
FM24V01A-GTR	51-85066	8-pin SOIC	

All these parts are Pb-free. Contact your local Cypress sales representative for availability of these parts.

## **Ordering Code Definitions**

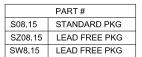


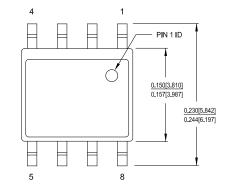


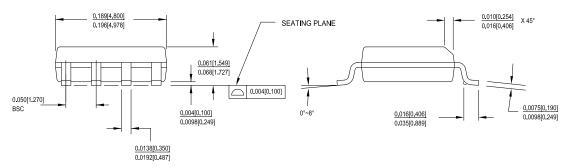
## **Package Diagram**

Figure 21. 8-pin SOIC (150 Mils) Package Outline, 51-85066

- 1. DIMENSIONS IN INCHES[MM]  $\frac{\text{MIN.}}{\text{MAX.}}$
- PIN 1 ID IS OPTIONAL,
   ROUND ON SINGLE LEADFRAME
   RECTANGULAR ON MATRIX LEADFRAME
- 3. REFERENCE JEDEC MS-012
- 4. PACKAGE WEIGHT 0.07gms







51-85066 \*I

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## **Acronyms**

Acronym	Description		
ACK	Acknowledge		
CMOS	Complementary Metal Oxide Semiconductor		
EIA	Electronic Industries Alliance		
I <sup>2</sup> C	Inter-Integrated Circuit		
I/O	Input/Output		
JEDEC	Joint Electron Devices Engineering Council		
LSB	Least Significant Bit		
MSB	Most Significant Bit		
NACK	No Acknowledge		
RoHS	Restriction of Hazardous Substances		
R/W	Read/Write		
SCL	Serial Clock Line		
SDA	Serial Data Access		
SOIC	Small Outline Integrated Circuit		
WP	Write Protect		

## **Document Conventions**

## **Units of Measure**

Symbol	Unit of Measure			
°C	degree Celsius			
Hz	hertz			
Kb	1024 bit			
kHz	kilohertz			
kΩ	kilohm			
MHz	megahertz			
ΜΩ	megaohm			
μΑ	microampere			
μS	microsecond			
mA	milliampere			
ms	millisecond			
ns	nanosecond			
Ω	ohm			
%	percent			
pF	picofarad			
V	volt			
W	watt			



## **Document History Page**

Rev.	ECN No.	Orig. of	Submission	Description of Change
	ECIVINO.	Change	Date	Description of Change
**	4266210	GVCH	01/29/2014	New data sheet.
*A	4390913	GVCH	06/20/2014	Changed status from Advance to Preliminary. Updated Maximum Ratings: Removed "Machine Model" under "Electrostatic Discharge Voltage". Updated DC Electrical Characteristics: Added typical values for $I_{SB}$ and $I_{ZZ}$ parameters. Splitted $V_{IH}$ parameter into two rows namely "SDL, SDA" and "WP, A2–A0". Changed maximum value of $V_{IH}$ parameter from " $V_{DD}$ + 0.5 V" to " $V_{DD}$ (max) + 0.3 V" corresponding to "SDL, SDA" and from " $V_{DD}$ + 0.5 V" to " $V_{DD}$ + 0.3 V" corresponding to "WP, A2–A0". Changed minimum value of $V_{IL}$ parameter from –0.5 V to –0.3 V. Renamed $V_{OL1}$ as $V_{OL}$ parameter. Added details of $V_{OL}$ parameter corresponding to Test Condition " $I_{OL}$ = 6 mA" Removed $V_{OL2}$ parameter and its details. Added $V_{IV}$ parameter and its details. Updated Capacitance: Removed $V_{OL2}$ parameter and its details. Updated AC Switching Characteristics: Added maximum values for $V_{AA}$ , $V_{VD;ACK}$ , $V_{OF}$ , $V_{CF}$ ,
*B	4512788	GVCH	09/24/2014	and its reference in t <sub>SU;DAT</sub> parameter.  Updated DC Electrical Characteristics:  Added Note 3 and referred the same note in V <sub>OL</sub> parameter.
*C	4571858	GVCH	11/18/2014	Updated DC Electrical Characteristics: Changed minimum value of V <sub>hys</sub> parameter from "0.1 × V <sub>DD</sub> " to "0.05 × V <sub>DD</sub> " corresponding to Test Condition "f <sub>SCL</sub> = 3.4 MHz". Added Note 5 and referred the same note in V <sub>hys</sub> parameter.
*D	4596783	GVCH	12/17/2014	Updated Features: Added Note 1 and referred the same note in "Up to 3.4-MHz frequency". Updated Two-wire Interface: Updated description (Added description for the difference in I <sub>OL</sub> and V <sub>hys</sub> with respect to NXP I <sup>2</sup> C specification). Updated DC Electrical Characteristics: Changed minimum value of V <sub>hys</sub> parameter from "0.05 × V <sub>DD</sub> " to "0.06 × V <sub>DD</sub> " corresponding to Test Condition "f <sub>SCL</sub> = 3.4 MHz". Updated Note 3. Updated Note 5. Updated to new template. Completing Sunset Review.
*E	4651363	ZSK	02/10/2015	Changed status from Preliminary to Final. Updated Functional Description: Added "For a complete list of related resources, click here." at the end. Updated Package Diagram: spec 51-85066 – Changed revision from *F to *G.



## **Document History Page** (continued)

	ocument Title: FM24V01A, 128-Kbit (16K × 8) Serial (I <sup>2</sup> C) F-RAM ocument Number: 001-90869					
Rev.	ECN No.	Orig. of Change	Submission Date	Description of Change		
*F	4874478	ZSK / PSR	08/06/2015	Updated Maximum Ratings: Removed "Maximum junction temperature" and its corresponding details. Added "Maximum accumulated storage time" and its corresponding details. Added "Ambient temperature with power applied" and its corresponding details.		
*G	5006363	GVCH	11/07/2015	Updated AC Switching Characteristics: Updated Figure 18 (Fixed typo (Changed the timing reference from t <sub>SU:SDA</sub> to t <sub>SU:STA</sub> )). Updated Figure 19 (Made t <sub>HD:STA</sub> parameter visible in diagram). Updated Package Diagram: spec 51-85066 – Changed revision from *G to *H. Completing Sunset Review.		
*H	5085665	GVCH	01/14/2016	Updated Ordering Information: Updated part numbers.		
*	5452467	ZSK	09/28/2016	Updated Power Cycle Timing: Changed minimum value of t <sub>PU</sub> parameter from 1 ms to 250 μs. Updated to new template.		
*J	6083747	GVCH	02/28/2018	Updated Package Diagram: spec 51-85066 – Changed revision from *H to *I. Updated to new template.		
*K	6422002	GVCH	12/26/2018	Updated Maximum Ratings: Replaced "–55 °C to +125 °C" with "–65 °C to +125 °C" in ratings corresponding to "Storage temperature". Updated to new template. Completing Sunset Review.		

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